

10/560706

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		Applicants: Takefumi NISHIMUTA; Hiroshi MIYAGI; Tadahiro OHMI; Shigetoshi SUGAWA; and Akinobu TERAMOTO				
		Filing Date: 07/24/06 Herewith		Group Art Unit: 2811 To Be Assigned		
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/A.B./	2002-359293	December 13, 2002	JAPAN	H 01 L	21 / 8238	Accompanied by US Publication No. 2002/0185676
/A.B./	8-264764	October 11, 1996	JAPAN	H 01 L	29 / 78	Accompanied by English abstract
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/A.B./	Partial English translation of office action for corresponding Taiwanese Patent Application and Taiwanese Office Action.					
/A.B./	Hisamoto et al, "FinFET - A Self-Aligned Double-Gate MOSFET Scalable to 20nm", <i>IEEE Transactions on Electron Devices</i> , Vol 47, No. 12, pps 2320-2325, December 12, 2000					
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Examiner	/Alexander Belousov/			Date Considered	10/29/2007	
EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP §609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to Applicant.						

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Serial No.:

10/560,706

Takefumi NISHIMUTA, et al.

Group Art Unit:

~~DBA~~

2811

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/A.B./	1	Taiwanese Office Action, dated December 29, 2005, issued in counterpart application.

/Alexander Belousov/

10/29/2007

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